

MiniSKiiP® 3

3-phase bridge inverter

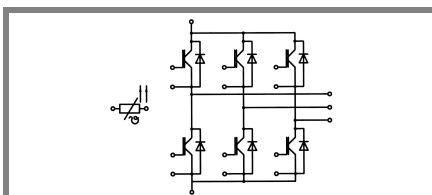
SKiiP 39AC066V4

Features

- Trench IGBTs
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Remarks

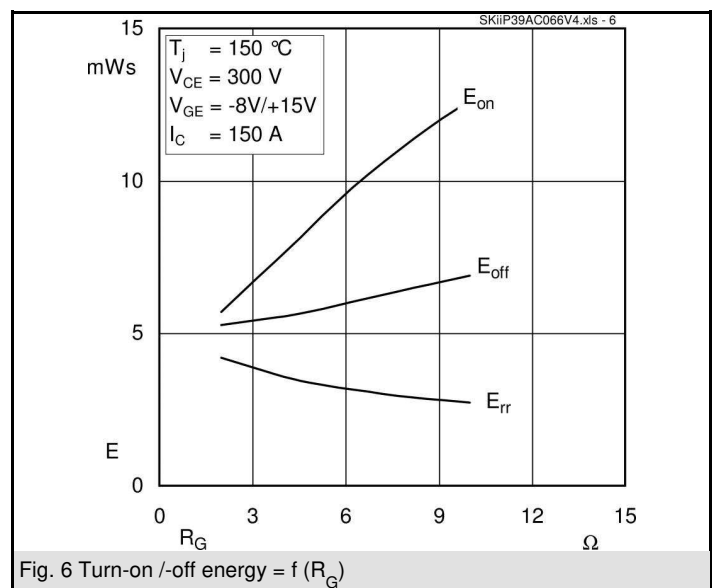
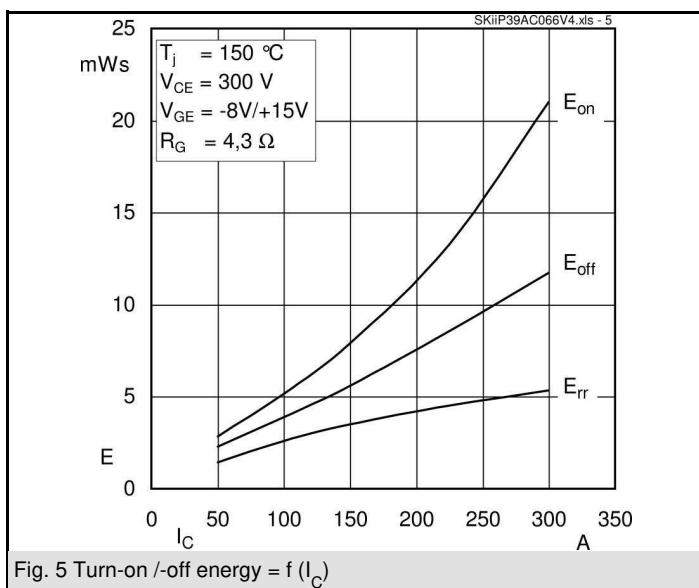
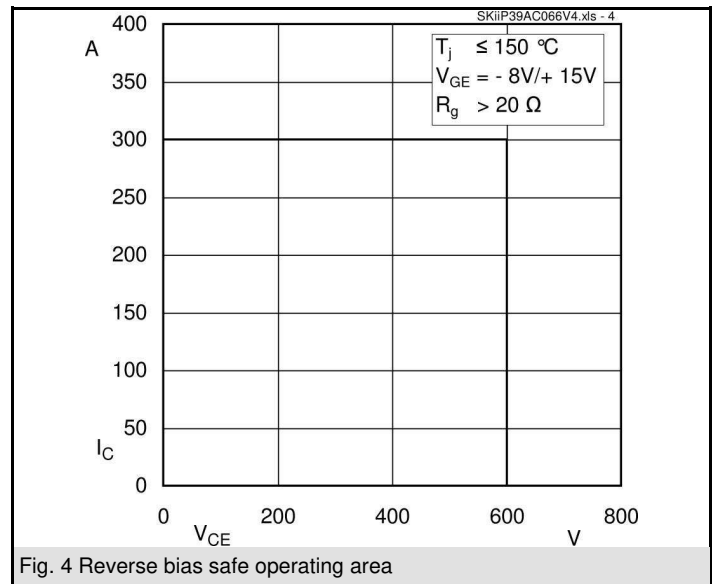
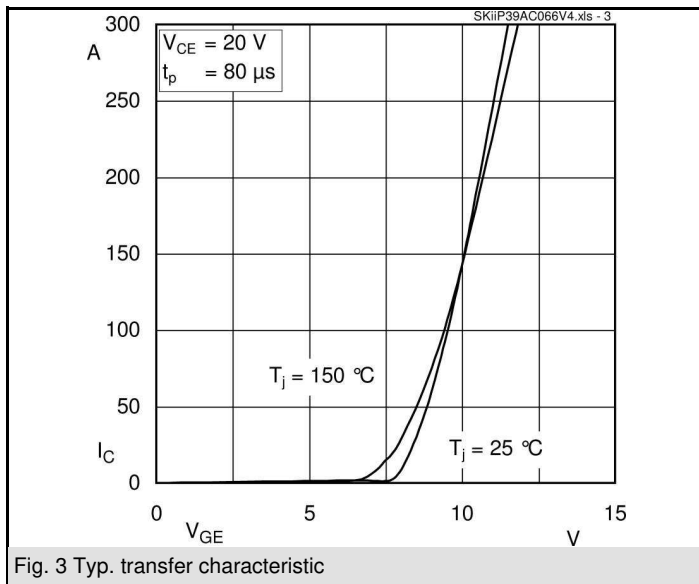
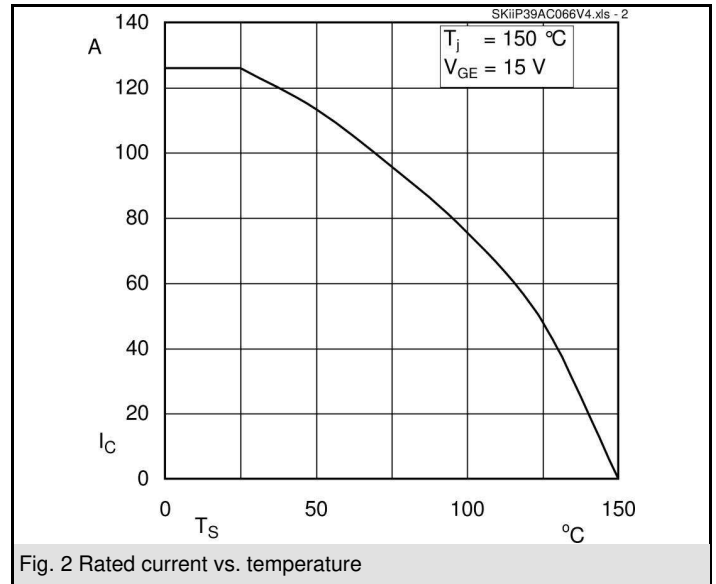
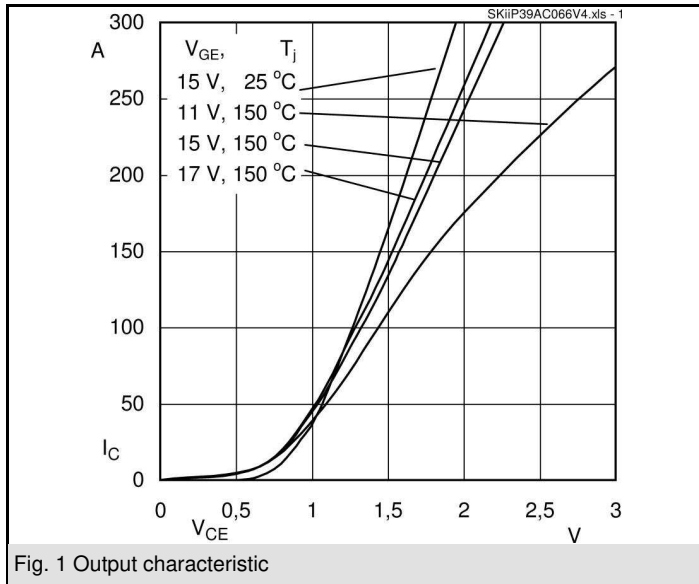
- Case temperature limited to $T_C = 125^\circ\text{C}$
- Product reliability results are valid for $T_j = 150^\circ\text{C}$
- SC data: $t_p \leq 6 \mu\text{s}$; $V_{GE} \leq 15 \text{ V}$; $T_j = 150^\circ\text{C}$, $V_{CC} = 360 \text{ V}$
- V_{CEsat} , V_F = chip level value



AC

Absolute Maximum Ratings		$T_S = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT - Inverter			
V_{CES}		600	V
I_C	$T_S = 25 (70)^\circ\text{C}$, $T_j = 150^\circ\text{C}$	131 (87)	A
I_C	$T_S = 25 (70)^\circ\text{C}$, $T_j = 175^\circ\text{C}$	146 (107)	A
I_{CRM}	$t_p = 1 \text{ ms}$	300	A
V_{GES}		± 20	V
T_j		-40...+175	$^\circ\text{C}$
Diode - Inverter			
I_F	$T_S = 25 (70)^\circ\text{C}$, $T_j = 150^\circ\text{C}$	151 (98)	A
I_F	$T_S = 25 (70)^\circ\text{C}$, $T_j = 175^\circ\text{C}$	164 (119)	A
I_{FRM}	$t_p = 1 \text{ ms}$	300	A
T_j		-40...+175	$^\circ\text{C}$
I_{RMS}	per power terminal (20 A / spring)	160	A
T_{stg}	$T_{op} \leq T_{stg}$	-40...+125	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		$T_S = 25^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT - Inverter					
V_{CEsat}	$I_{Cnom} = 150 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$	1,05	1,45 (1,65)	1,85 (2,05)	V
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 3 \text{ mA}$		5,8		V
$V_{CE(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,85 (0,7)	1,1 (1)	V
r_T	$T_j = 25 (150)^\circ\text{C}$		4 (6,3)	5 (7)	m Ω
C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		9		nF
C_{oes}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		1,7		nF
C_{res}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$		1,4		nF
$R_{CC+EE'}$	spring contact-chip $T_S = 25 (150)^\circ\text{C}$				m Ω
$R_{th(j-s)}$	per IGBT		0,5		K/W
$t_{d(on)}$	under following conditions		135		ns
t_r	$V_{CC} = 300 \text{ V}$, $V_{GE} = -8\text{V}/+15\text{V}$		55		ns
$t_{d(off)}$	$I_{Cnom} = 150 \text{ A}$, $T_j = 150^\circ\text{C}$		450		ns
t_f	$R_{Gon} = R_{Goff} = 4,3 \Omega$		50		ns
$E_{on}(E_{off})$	inductive load		7,9 (5,6)		mJ
Diode - Inverter					
$V_F = V_{EC}$	$I_{Fnom} = 150 \text{ A}$, $T_j = 25 (150)^\circ\text{C}$		1,3 (1,3)	1,5 (1,5)	V
$V_{(TO)}$	$T_j = 25 (150)^\circ\text{C}$		0,9 (0,8)	1 (0,9)	V
r_T	$T_j = 25 (150)^\circ\text{C}$		2,7 (3,3)	3,3 (4)	m Ω
$R_{th(j-s)}$	per diode		0,55		K/W
I_{RRM}	under following conditions		150		A
Q_{rr}	$I_{Fnom} = 150 \text{ A}$, $V_R = 300 \text{ V}$		17		μC
E_{rr}	$V_{GE} = 0 \text{ V}$, $T_j = 150^\circ\text{C}$ $di_F/dt = 3000 \text{ A}/\mu\text{s}$		3,5		mJ
Temperature Sensor					
R_{ts}	3 %, $T_r = 25 (100)^\circ\text{C}$		1000(1670)		Ω
Mechanical Data					
m			97		g
M_s	Mounting torque	2		2,5	Nm



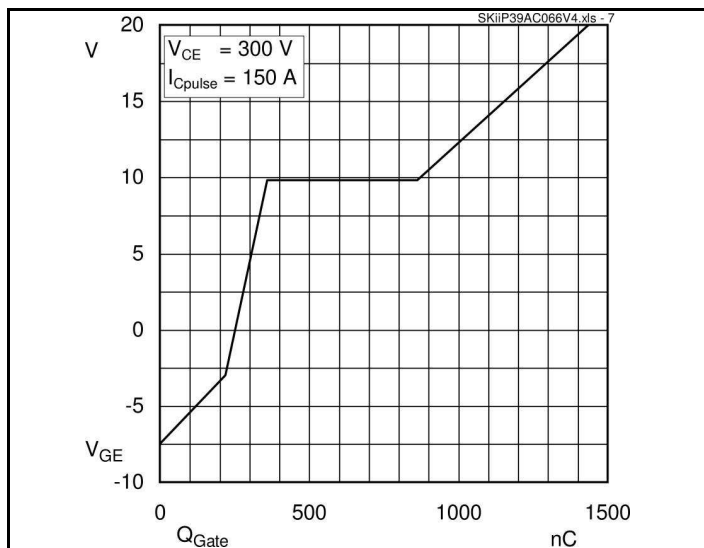


Fig. 7 Typ. Gate charge characteristic

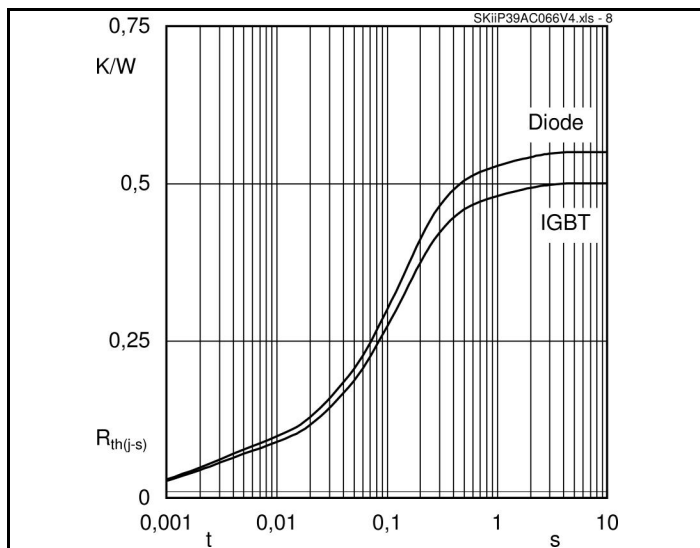


Fig. 8 Thermal impedance

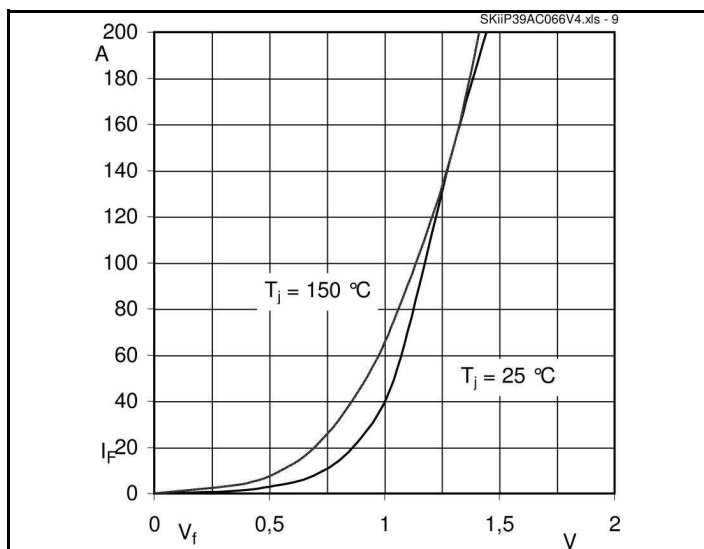


Fig. 9 Freewheeling diode forward characteristic

